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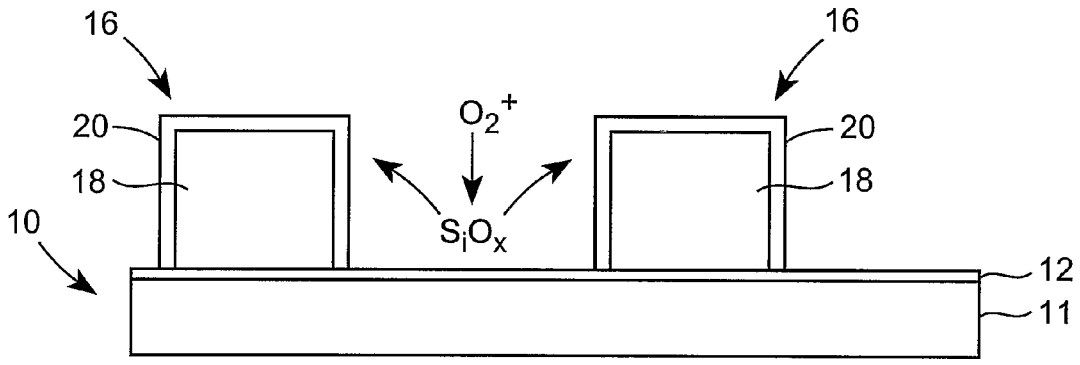
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(54) Title: METHODS OF REMOVING PHOTORESIST ON SUBSTRATES



(57) Abstract: Methods of etching a carbon-rich layer on organic photoresist overlying an inorganic layer can utilize a process gas including a fluorine-containing gas, an oxygen-containing gas, and a hydrocarbon gas, and one or more optional components to generate a plasma effective to etch the carbon-rich layer with low removal of the inorganic layer. The carbon-rich layer can be removed in the same processing chamber, or alternatively can be removed in a different processing chamber, as used to remove the bulk photoresist.

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